

RB521S-30

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

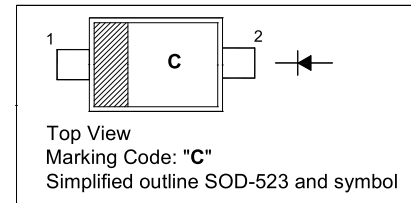
for low current rectification and high speed switching applications

Features

- Extremely small surface mounting type

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |



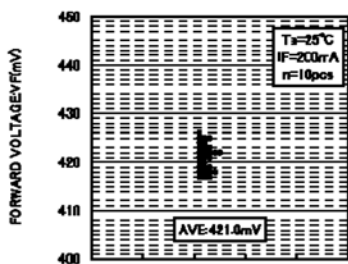
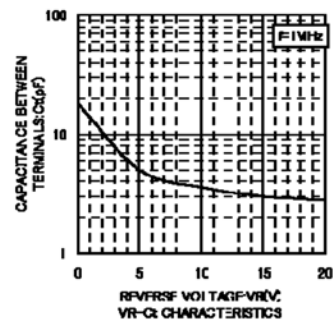
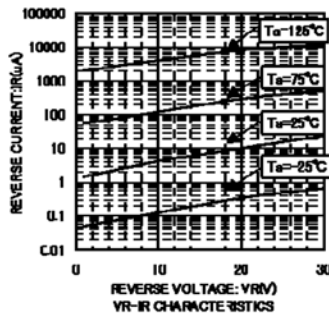
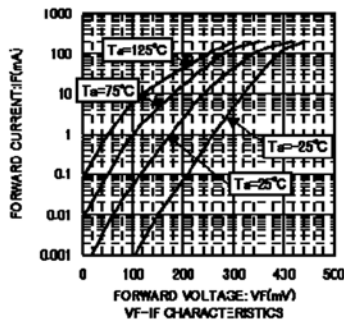
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--|-----------|---------------|------------------|
| Reverse Voltage | V_R | 30 | V |
| Mean Rectifying Current | I_O | 200 | mA |
| Peak Forward Surge Current (60Hz for Cyc.) | I_{FSM} | 1 | A |
| Junction Temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 40 to + 125 | $^\circ\text{C}$ |

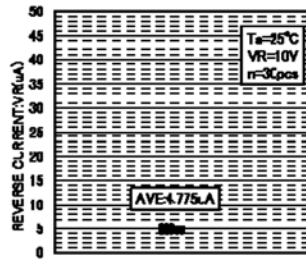
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Max. | Unit |
|---|--------|------|---------------|
| Forward Voltage at $I_F = 200\text{ mA}$ | V_F | 0.5 | V |
| Reverse Current at $V_R = 10\text{ V}$ | I_R | 30 | μA |

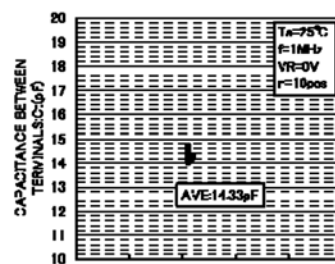
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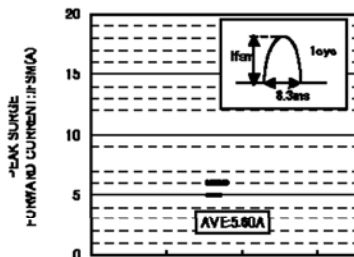
VF DISPERSION MAP



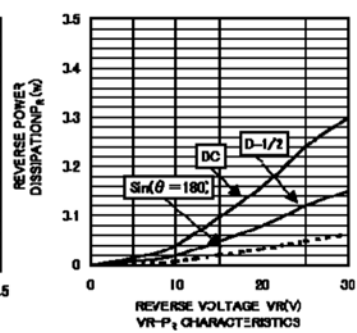
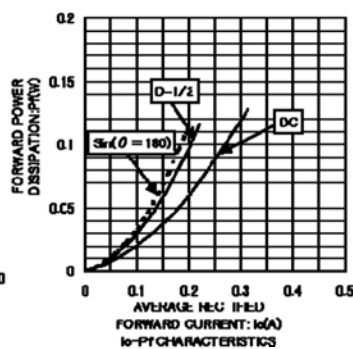
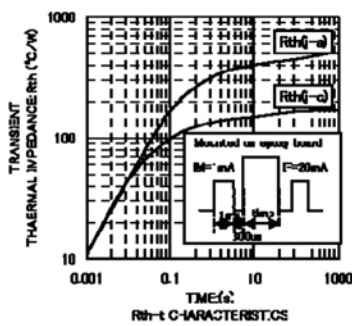
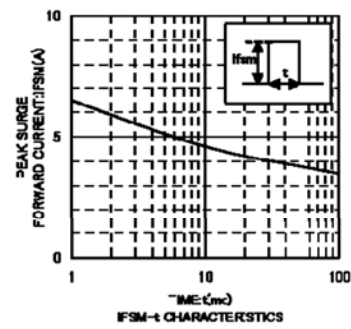
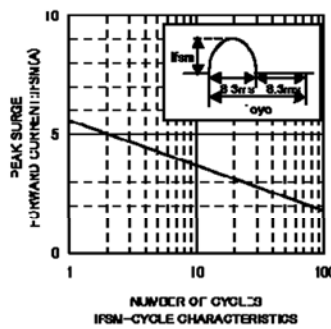
IR DISPERSION MAP



C_j DISPERSION MAP



IFSM DISPERSION MAP

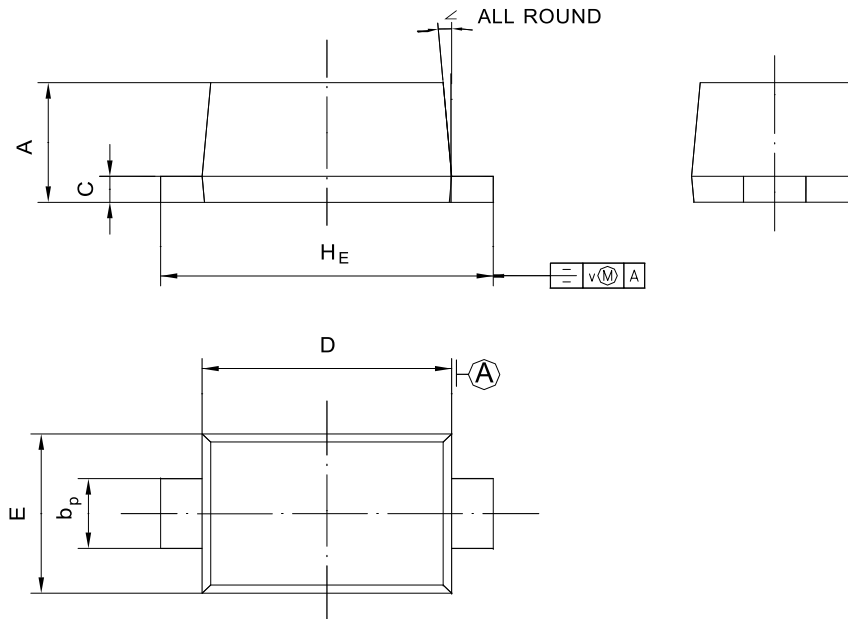


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



| UNIT | A | b _p | C | D | E | H _E | V | ∠ |
|------|--------------|----------------|----------------|--------------|--------------|----------------|-----|----|
| mm | 0.70 0.60 | 0.4 0.3 | 0.135 0.100 | 1.25 1.15 | 0.85 0.75 | 1.7 1.5 | 0.1 | 5° |